

49.18

( )	12.16					
A ( )	2.37					
( )	597.99					
( )	63.56/41.30	( )	2018	2019	2020E	2021E
300	4568	( )	6,271	5,743	6,668	7,644
	3228	( )	6.73%	-8.42%	16.11%	14.65%
		( )	429	401	673	767
		( )	511.02%	-6.68%	67.95%	13.89%
		( )	0.489	0.456	0.554	0.630
		( )	n.a	0.69	0.71	0.98
		ROE( ) ( )	10.35%	7.39%	6.64%	7.22%
						8,730
						14.20%
						11.57%
						0.703
						1.10
						7.68%

	2020				
16.0%	4.0	30.6			
16.8	15.6%	145%			
81.7%		3.2			
<b>IDM</b>					
29.3%	2019				
	12.8%	<b>IDM</b>			20%
1.					
2020.4.23					
2.					
<b>IDM</b>	2020				
2020.3.25	44.95%	1.55			13.69
		22.3%	<b>MOSFET</b>		
	<b>IGBT</b>	49.9%			21.4%
	6.9%	<b>SiC</b>			
	13.4%				20%

2017	2018	2019	2020E	2021E	2022E
<b>5,876</b>	<b>6,271</b>	<b>5,743</b>	<b>6,668</b>	<b>7,644</b>	<b>8,730</b>
	6.7%	-8.4%	16.1%	14.6%	14.2%

2017	2018	2019	2020E	2021E	2022E
1,219	1,538	1,931	5,985	5,662	5,753
2,392	2,292	1,504			

0	0	0	0	0
0	0	0	0	0
0	0	0	0	0
0	0	0	0	0
<b>0.00</b>	<b>0.00</b>	<b>0.00</b>	<b>0.00</b>	<b>0.00</b>

	2	3	1	4
1.00 =	1.01~2.0=	2.01~3.0=		
3.01~4.0=				

( )

1	2020-03-25	52.30	52.30
2	2020-04-23	52.30	52.30

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